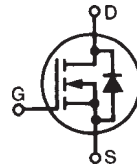


**TrenchMV™ Power  
MOSFET HiperFET™**
**IXFA130N10T  
IXFP130N10T**

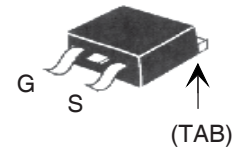
 N-Channel Enhancement Mode  
Avalanche Rated  
Fast intrinsic diode


$$V_{DSS} = 100V$$

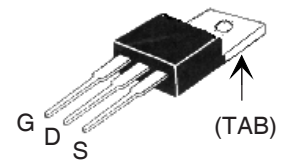
$$I_{D25} = 130A$$

$$R_{DS(on)} \leq 9.1m\Omega$$

TO-263 (IXFA)



TO-220 (IXFP)


 G = Gate    D = Drain  
S = Source    TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $175^\circ C$	100	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ C$	130	A
$I_{LRMS}$	Lead Current Limit, RMS	75	A
$I_{DM}$	$T_C = 25^\circ C$ , pulse width limited by $T_{JM}$	350	A
$I_A$	$T_C = 25^\circ C$	65	A
$E_{AS}$	$T_C = 25^\circ C$	750	mJ
$P_D$	$T_C = 25^\circ C$	360	W
$T_J$		-55 ... +175	$^\circ C$
$T_{JM}$		175	$^\circ C$
$T_{stg}$		-55 ... +175	$^\circ C$
$T_L$	1.6mm (0.062 in.) from case for 10s	300	$^\circ C$
$T_{SOLD}$	Plastic body for 10 seconds	260	$^\circ C$
$M_d$	Mounting torque (TO-220)	1.13 / 10	Nm/lb.in.
Weight	TO-220	3.0	g
	TO-263	2.5	g

**Features**

- Ultra-low On Resistance
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect
- 175  $^\circ C$  Operating Temperature
- Fast intrinsic diode

**Advantages**

- Easy to mount
- Space savings
- High power density

**Applications**

- Automotive
  - Motor Drives
  - 42V Power Bus
  - ABS Systems
- DC/DC Converters and Off-line UPS
- Primary Switch for 24V and 48V Systems
- Distributed Power Architectures and VRMs
- Electronic Valve Train Systems
- High Current Switching Applications
- High Voltage Synchronous Rectifier

Symbol	Test Conditions ( $T_J = 25^\circ C$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 1mA$	2.5		V
$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ $V_{GS} = 0V$ $T_J = 150^\circ C$			10 $\mu A$
				500 $\mu A$
$R_{DS(on)}$	$V_{GS} = 10V, I_D = 25A$ , Notes 1, 2			9.1 m $\Omega$

Symbol	Test Conditions	Characteristic Values			
		Min.	Typ.	Max.	
$(T_J = 25^\circ\text{C unless otherwise specified})$					
$g_{fs}$	$V_{DS} = 10\text{V}, I_D = 60\text{A}, \text{Note 1}$	55	93		S
$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		5080		pF
$C_{oss}$			630		pF
$C_{rss}$			95		pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 25\text{A}$ $R_G = 5\Omega \text{ (External)}$		30		ns
$t_r$			47		ns
$t_{d(off)}$			44		ns
$t_f$			28		ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 25\text{A}$		104		nC
$Q_{gs}$			30		nC
$Q_{gd}$			29		nC
$R_{thJC}$				0.42	$^\circ\text{C/W}$
$R_{thCH}$	TO-220	0.50			$^\circ\text{C/W}$

**Source-Drain Diode**

Symbol	Test Conditions	Characteristic Values			
		Min.	Typ.	Max.	
$T_J = 25^\circ\text{C unless otherwise specified}$					
$I_S$	$V_{GS} = 0\text{V}$			130	A
$I_{SM}$	Repetitive, pulse width limited by $T_{JM}$			350	A
$V_{SD}$	$I_F = 25\text{A}, V_{GS} = 0\text{V}, \text{Note 1}$			1.0	V
$t_{rr}$	$I_F = 65\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 0.5 \cdot V_{DSS}, V_{GS} = 0\text{V}$		67		ns
$I_{RM}$			4.7		A
$Q_{rr}$			160		nC

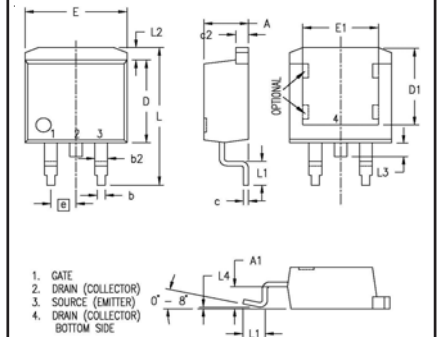
- Notes: 1. Pulse test,  $t \leq 300 \mu\text{s}$ ; duty cycle,  $d \leq 2\%$ .  
 2. On through-hole packages,  $R_{DS(on)}$  Kelvin test contact location must be 5 mm or less from the package body.

**PRELIMINARY TECHNICAL INFORMATION**

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

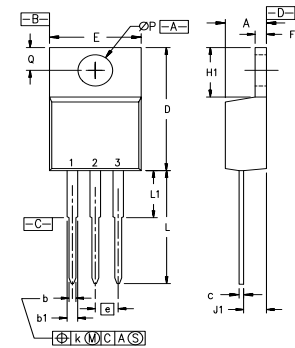
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

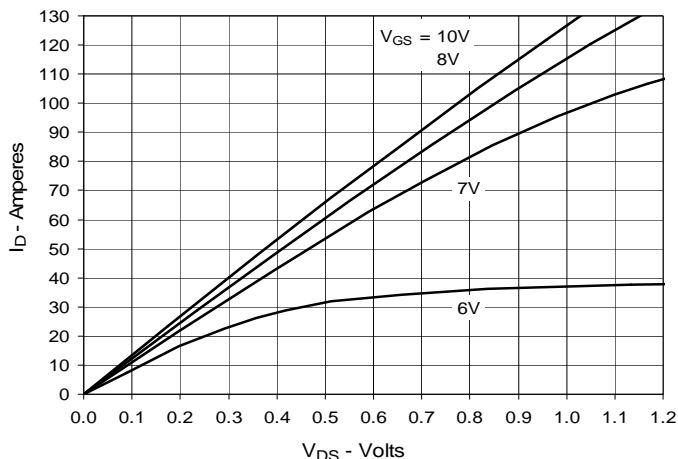
**TO-263 (IXFA) Outline**


- Pins: 1 - Gate 2 - Drain  
 3 - Source 4, TAB - Drain

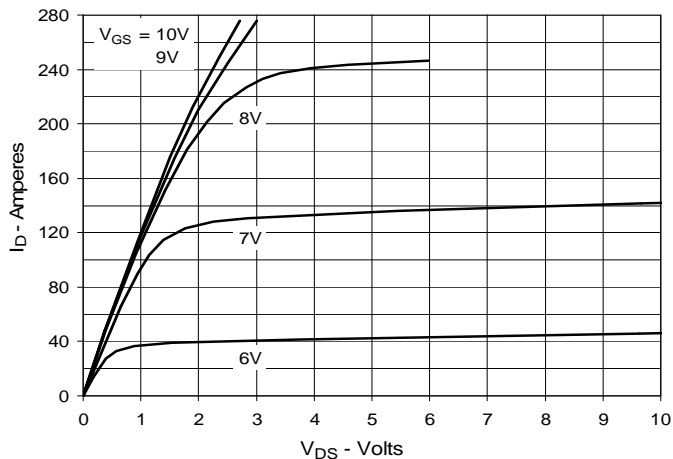
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
E	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029

**TO-220 (IXFP) Outline**


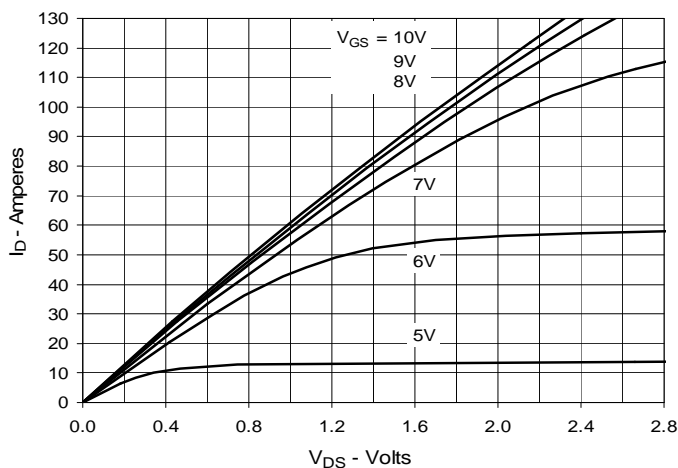
**Fig. 1. Output Characteristics @ 25°C**



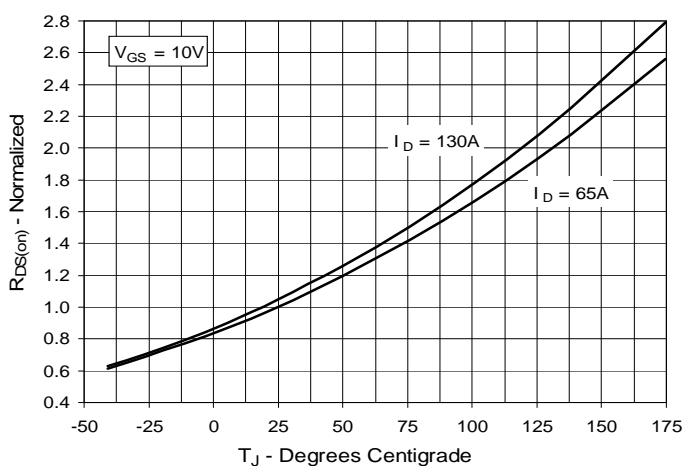
**Fig. 2. Extended Output Characteristics @ 25°C**



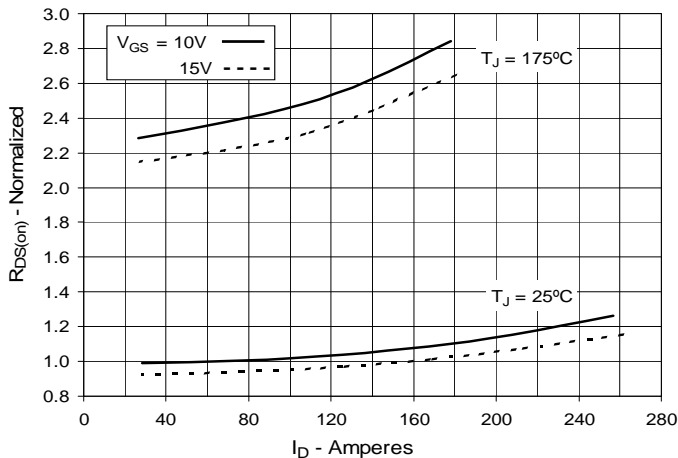
**Fig. 3. Output Characteristics @ 150°C**



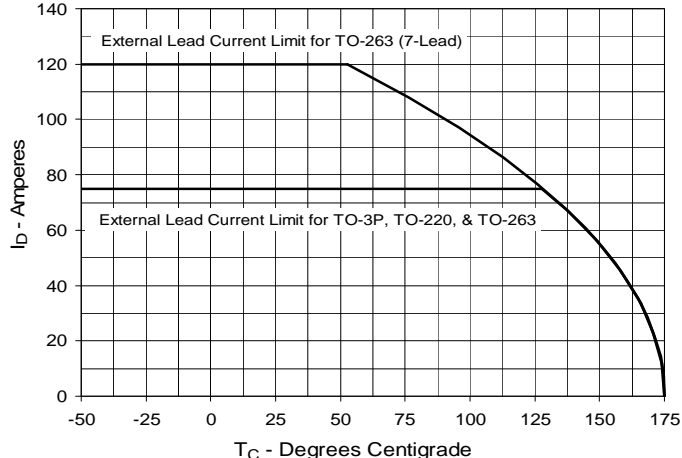
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 65A$  Value vs. Junction Temperature**



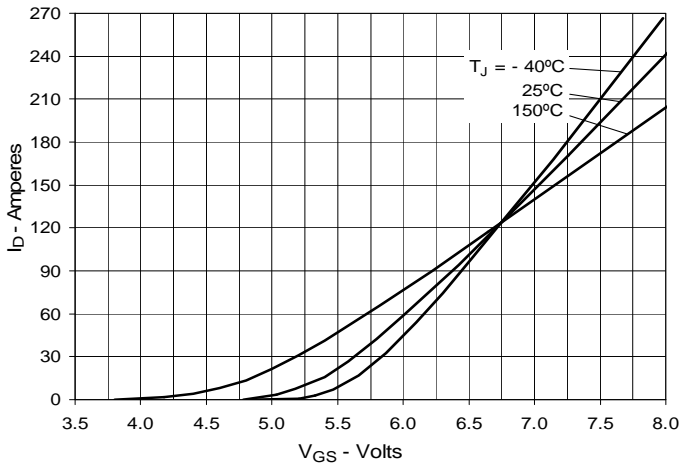
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 65A$  Value vs. Drain Current**



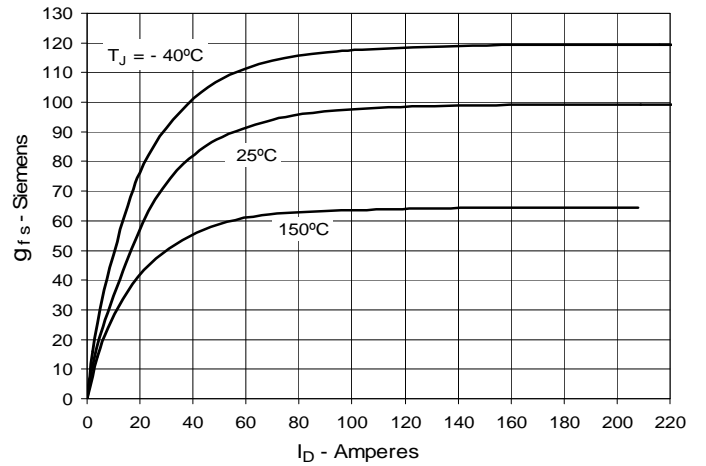
**Fig. 6. Drain Current vs. Case Temperature**



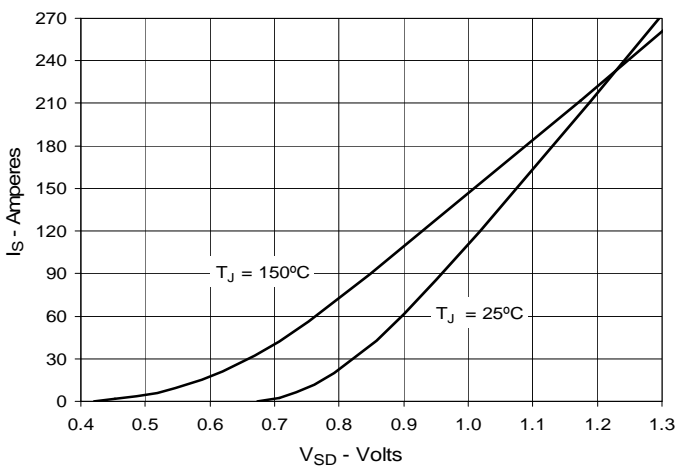
**Fig. 7. Input Admittance**



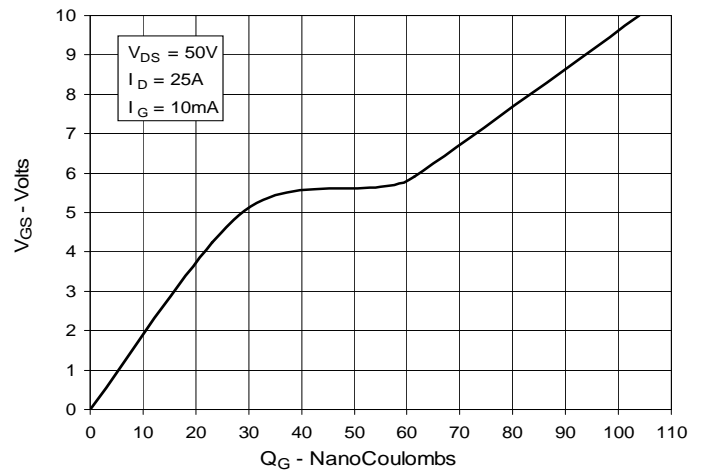
**Fig. 8. Transconductance**



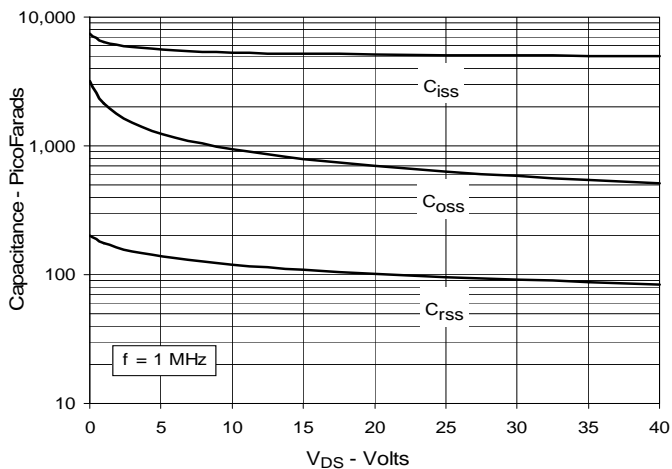
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



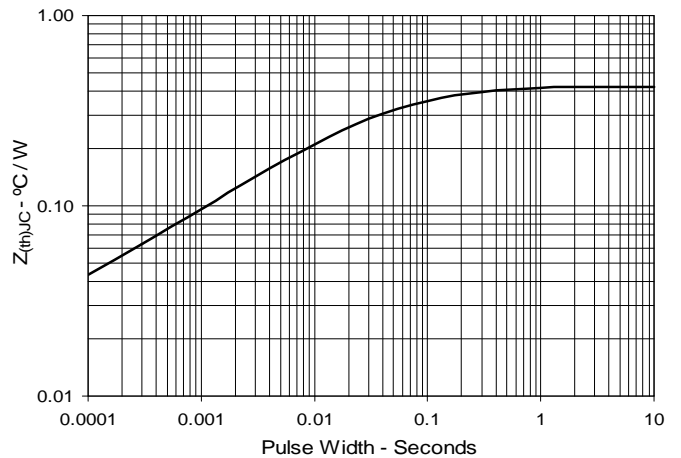
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**

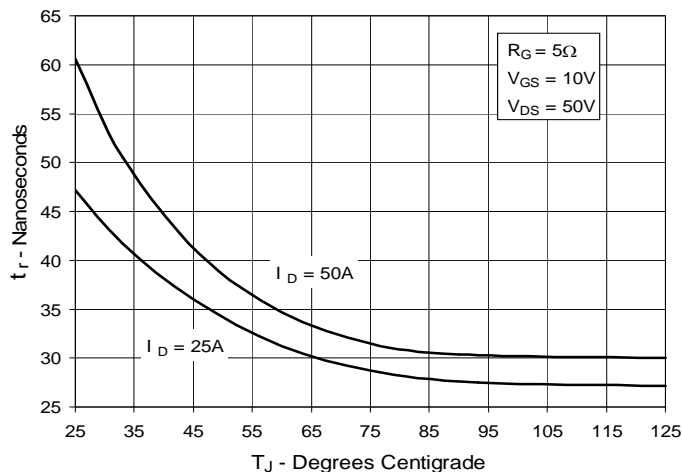


**Fig. 12. Maximum Transient Thermal Impedance**

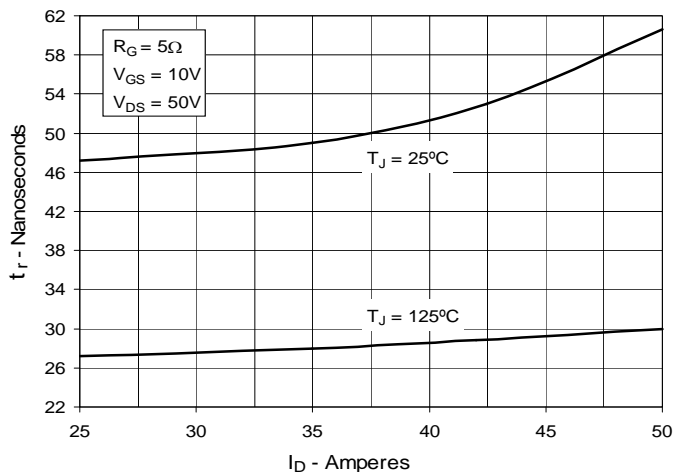


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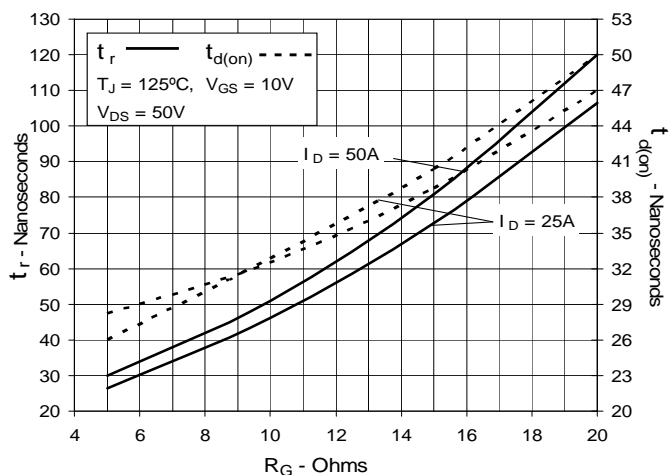
**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**



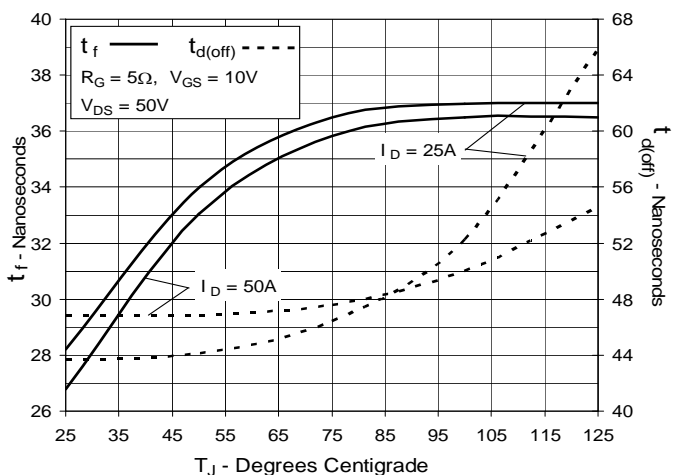
**Fig. 14. Resistive Turn-on Rise Time vs. Drain Current**



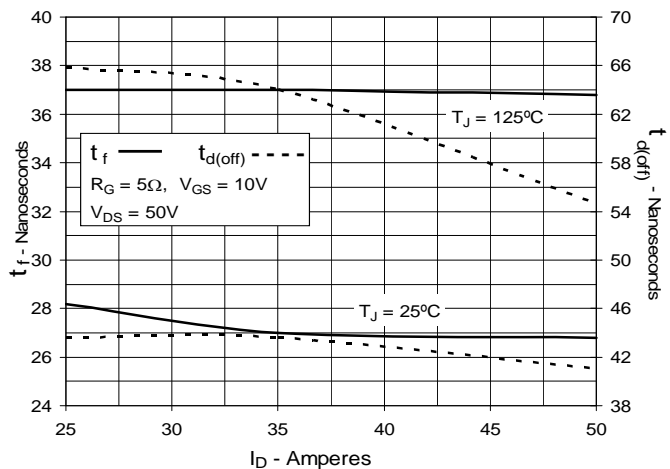
**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**



**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**

